

# 5/IDS

Sheet 1 of 7

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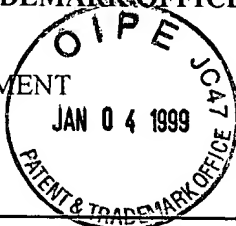
HARI.006USS

SERIAL NO.

09/129,675

## INFORMATION DISCLOSURE STATEMENT

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ELIYAHOU HARARI et al.

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## U. S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
at	A5	4 0 9 0 2 5 8	5/16/78	Cricchi	365	184	
	A6	4 1 4 9 2 7 0	4/10/79	Cricchi et al.	365	222	
	A7	4 1 8 1 9 8 0	1/1/80	McCoy	365	45	
	A8	4 2 5 3 0 5 9	2/24/81	Bell et al.	365	721	
	A9	4 2 7 2 8 3 0	6/9/81	Moench	365	45	
	A10	4 2 7 9 0 2 4	7/14/81	Schrenk	365	185.22	
	A11	4 2 8 7 5 7 0	9/1/81	Stark	365	104	
	A12	4 3 9 3 4 7 5	7/12/83	Kitagawa et al.	365	185.21	
	A13	4 4 1 5 9 9 2	11/15/83	Adlhoch	365	94	
	A14	4 4 6 0 9 8 2	7/17/84	Gee et al.	365	185.19	
at	A15	4 4 9 5 6 0 2	1/22/85	Sheppard	365	104	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANS.? (YES/NO)
at	B1	GB 2 0 6 1 6 5 1	5/1981	United Kingdom	611C	7/00	
	B2	GB 2 0 2 9 1 4 5	3/1980	United Kingdom	611C	17/00	
	B3	JP 6 2 2 5 7 6 99	11/1987	Japan	611C	17/00	Abstract
	B4	JP 5 9 3 1 1 5 8	2/1984	Japan	B32B	035/00	Abstract
at	B5	DE 3 6 3 7 6 8 2	5/1987	Germany	611C	17/00	Abstract

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

at	C1	Bleiker et al., "A Four-State EEPROM Using Floating-Gate Memory Cells", IEEE Journal of Solid-State Circuits, vol. sc-22, No. 3, June 1987, pp. 460-463.
at	C2	Torelli et al., "An Improved Method for Programming a Word-Erasable EEPROM", Alta Frequenza, Vol. 52, Nov. - Dec. 1983, no. 6, pp. 487-494.
at	C3	Stark, "Two Bits Per Cell ROM", Digest of Papers of Spring COMPCONS 81, Feb. 23-26, VLSI LABORATORY, pp. 209-212.

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at	A16	4 5 8 6 1 6 3	4/29/86	Koike	365	104	
	A17	4 6 1 2 6 2 9	9/16/86	Harari	365	185.08	
	A18	4 7 1 8 0 4 1	1/5/88	Baglee et al.	365	185.22	
	A19	4 7 3 3 3 9 4	3/22/88	Giebel	714	711	
	A20	4 7 5 2 9 2 9	6/21/88	Kantz et al.	714	719	
	A21	4 7 6 3 3 0 5	8/9/88	Kuo	365	185.22	
	A22	4 7 7 9 2 7 2	10/18/88	Kohda et al.	714	721	
	A23	4 7 9 9 1 9 5	1/17/89	Iwahashi et al.	365	185.21	
	A24	4 8 0 7 1 8 8	2/21/89	Casagrande	365	185.05	
	A25	4 8 0 9 2 3 1	2/28/89	Shannon et al.	365	201	
at	A26	4 8 1 1 2 9 4	3/7/89	Kobayashi et al.	365	185.22	

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANS? (YES/NO)
at	B6	DE 3 8 3 1 5 3 8	3/1989	Germany	611C	17/06	Abstract
	B7	JP 62 1 8 8 1 0 0	8/1987	Japan	611C	17/00	Abstract
	B8	JP 0 1 2 3 8 7 8	5/1989	Japan	611C	11/34	Abstract
at	B9	JP 0 1 4 6 9 4 9	10/1989	Japan	611C	11/34	Abstract

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

at	C4	Furuyama et al, "An Experimental 2-BIT/CELL Storage Dram for Macro Cell or Memory-on-Logic Application", IEEE Custom Integrated Circuits Conference, May 1988, pp. 4.4.1 - 4.4.4
at	C5	Krick, "Three-State MNOS FET Memory Array", IBM Technical Disclosure Bulletin, Vol. 18, No. 12, May 1976, pp. 4192-4193.
at	C6	Alberts et al, "Multi-Bit Storage Fet Earom Cell" IBM Technical Disclosure Bulletin," Vol. 24, No. 7A, Dec 1981, pp. 3311-3314, 4193.

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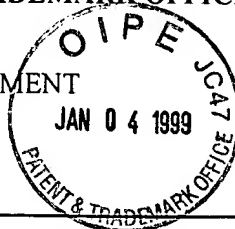
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at	A27	4 8 4 7 8 0 8	7/11/89	Kobatake	365	104	
	A28	4 8 7 0 6 1 8	9/26/89	Iwashita	365	185.18	
	A29	4 9 4 3 9 6 2	7/24/90	Imamiya et al.	365	230.08	
	A30	4 9 5 6 8 1 6	9/11/90	Atsumi et al.	365	185.22	
	A31	4 9 9 9 8 1 3	3/12/91	Ohtsuka et al.	365	185.18	
	A32	5 0 0 3 5 1 0	3/26/91	Kamisaki	365	189.01	
	A33	5 0 5 3 9 9 0	10/1/91	Kreifels et al.	711	103	
	A34	5 0 9 5 3 4 4	3/10/92	Harari	365	185.03	
	A35	5 1 6 3 0 2 1	11/10/92	Mehrotra et al.	714	710	
	A36	5 2 9 7 1 4 8	3/22/94	Harari et al.	365	185.22	
at	A37	5 3 5 7 4 6 2	10/18/94	Tanaka et al.			

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at	C7	Horiguchi et al., "An Experimental Large-Capacity Semiconductor File Memory Using 16-LEVELS/CELL Storage" IEEE Journal of Solid-State Circuits, Vol. 23, Feb 1988, No. 1, pp. 27-33.
at	C8	Masuoka et al., "A 256-KBIT Flash EEPROM using Triple-Polysilicon Technology" IEEE Journal of Solid-State Circuits, vol.SC-22, no.4, pp 548-552, New York, US, August 1987
at	C9	Berenga et al., "E2-PROM TV Synthesizer", 1978 IEEE International Solid-State Circuits Conference: ISCCC 78," February 17, 1978, pp.196-197.

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at	A38 5 3 6 1 2 2 7	1/1/94	Tanaka et al.	365	185.22	
	A39 5 6 0 2 9 8 7	2/11/97	Harari et al.	714	8	
	A40 4 9 5 9 8 1 2	9/25/90	Momodomi et al.	365	185.17	
	A41 4 9 3 9 6 9 0	7/3/90	Momodomi et al.	365	185.17	
at	A42 4 9 9 6 6 6 9	2/26/91	Endoh et al.	365	185.17	

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## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

at	C10	Kynett et al., "An In-System Reprogrammable 32K X 8 CMOS Flash Memory", IEEE Journal of Solid-State Circuits, Vol. 23, No. 5, Log Number 8822443, October 1988, pp. 1157-1163.
at	C11	Klingman, "Microprocessor Systems Design" Prentice-Hall Inc., pp. 30-31, 1977.
at	C12	SGS-Ates, "Excerpts From a 1983 Data Book" SGS-Ates Group, 45 pp., Nov. 1983.
at	C13	SINGLE CHIP INCLUDING Torelli et al, "Non-Volatile Station Memory and Remote Control Receiver and Memory-Display Driver" IEEE Transactions on Consumer Electronics, vol. CE-29, no. 3, pp. 103-113, August 1983.

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